G. Device & Process Modeling, Simulation and Reliability 분과

2021년 1월 28일(목), 10:45–12:15 / 채널 D

[TD2-G] Thin Film Transistors and Device Modeling

좌장: 나현철 상무 (DB하이텍), 백록현 교수 (POSTECH)

TD2-G-1 **10:45-11:00**	**Influence of the Oxygen Content on Hot Carrier Effects in the Bottom-gate Amorphous InGaZnO Thin-film Transistors** Je-Hyuk Kim, Jun Tae Jang, Dong Myong Kim, Sung-Jin Choi, Jong-Ho Bae, and Dae Hwan Kim *School of Electrical Engineering, Kookmin University*
TD2-G-2 **11:00-11:15**	**The Analysis of Band-gap State of Tensile Strained a-IGZO TFT Dependent on the Bending Direction and Channel Length** Yunyeong Choi[1], Jisun Park[1,2], and Hyungsoon Shin[1,2] *[1]Department of Electronic and Electrical Engineering, Ewha Womans University,* *[2]Smart Factory Multidisciplinary Program, Ewha Womans University*
TD2-G-3 **11:15-11:30**	**Experimental Observation of the Variation of Oxygen Vacancy-Related Density of States in InGaZnO TFTs under the Negative Bias Illumination Stress** Ga Won Yang, Jingyu Park, Sungju Choi, Dong Myong Kim, Sung-Jin Choi, Jong-Ho Bae, and Dae Hwan Kim *School of Electrical Engineering, Kookmin University*
TD2-G-4 **11:30-11:45**	**Compact Model of Cylindrical Gate-all-around MOSFETs based on the Density-gradient Equation** Kwang-Woon Lee and Sung-Min Hong *School of Electrical Engineering and Computer Science, GIST*
TD2-G-5 **11:45-12:00**	**Gate Voltage-dependent Extraction and Modeling for Junction Capacitance of MOSFETs** Jinwook Kuk and Seonghearn Lee *Department of Electronics Engineering, Hankuk University of Foreign Studies*
TD2-G-6 **12:00-12:15**	**BJT의 Base 구조에 따른 Matching 특성 분석** Seong-Hyun Kim, Hyun-Jin Shin, Ki-Woo Song, and Hi-Deok Lee *Chungnam National University*